

## Product Overview

### NXH006P120MNF2: SiC Modules, Half Bridge 2-PACK 1200 V, 6 mohm SiC MOSFET, F2 Package

For complete documentation, see the data sheet.

The NXH006P120MNF2 is a half-bridge or 2-PACK SiC Module with 2 6mohm 1200V SiC MOSFET switches and a thermistor in an F2 package. The SiC MOSFET switches use M1 technology and are driven with 18V-20V gate drive.

#### Features

- Robust M1 planar SiC MOSFET technology
- 18V to 20V gate drive

#### Benefits

- Improved reliability from planar technology and from lower die thermal resistance
- 20V operation for lower losses; 18V for compatibility with other modules

#### Applications

- DC-AC conversion
- DC-DC conversion
- AC-DC conversion

#### End Products

- UPS
- Energy Storage Systems
- Electric Vehicle Charging Stations
- Solar Inverters

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	V <sub>BR</sub> Max (V)	R <sub>DS(on)</sub> Typ (Ω)	Package Type
NXH006P120MNF2PTG	165.0472	Pb-free Halide free non AEC-Q and PPAP	Active	2-PACK	1200	6	PIM36 56.7x42.5 (PRESS FIT)

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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